Developer for AR E-Beam Resists

AR 600-50, 600-546, -548, -549, 600-55, -56 developer

For the development of e-beam resists films

Characterisation

- ultrapure, ultra-filtered (0.2 μm) solvent mixtures
- storage temperature at 10-22 °C

| Properties | safer | solvent optimally s | suited suited |
|----------------------------------|---|----------------------------------|----------------------------------|
| AR resist / developer | AR 600-50 | AR 600-55 | AR 600-56 |
| Fields of application/conditions | dip, puddle, spray development at 21-23 °C ± 1 °C | | |
| Main component(s) | methoxypropanol / isopro- pyl alcohol | methyl isobutyl ketone (MIBK) | methyl isobutyl ketone (MIBK) |
| Properties | | strong developer | weaker developer |
| Density at 20 °C (g/cm3) | 0.871 | 0.792 | 0.788 |
| Refractive index at 20 °C | 1.395 | 1.384 | 1.381 |
| Water content max. (%) | 0.1 | 0.1 | 0.1 |
| Flash point (°C) | 21 | 12 | 12 |
| AR-P 617 | 2-3 min | 3 min | 3 min |
| AR-P 630 - 670 series | - | 1-3 min | 1-3 min |
| AR-P 6500 | - | - | - |
| AR resist / developer | AR 600-546 | AR 600-548 | AR 600-549 |
| Fields of application/conditions | dip, puddle, spray development at 21-23 °C ± 1 °C | | |

| AR resist / developer | AR 600-546 | AR 600-548 | AR 600-549 |
|----------------------------------|---|--------------------------------------|-------------------------------|
| Fields of application/conditions | dip, puddle, spray development at 21-23 °C ± 1 °C | | |
| Main component(s) | amyl acetate | diethyl ketone / diethyl malonate | diethyl malonate / anisole |
| Properties | weaker developer | strong developer | moderate developer |
| Density at 20 °C (g/cm3) | 0.876 | 0.917 | 1.053 |
| Refractive index at 20 °C | 1.402 | 1.401 | 1.417 |
| Water content max. (%) | 0.1 | 0.1 | 0.1 |
| Flash point (°C) | 41 | 22 | 85 |
| AR-P 6200 | 1 min | 1 min | 1 min |

Information on developer processing

The choice of the developer strongly influences the development rate, the sensitivity and the profile of the resist structures. Coated and exposed substrates are treated with developers which are suitable for the respective process (puddle, spray, immersion bath) at a temperature of 21-23 $^{\circ}$ C kept as constant as possible. The required development time depends in each case on the resist film thickness. Films with a thickness of less than 0.2 μ m can for example be completely developed after 30 s. The development process can be slowed down for AR 600-50, -55 and -56 by adding 10-20 % of the stopper AR 600-60.

Weaker developers like AR 600-56 and AR 600-546 provide a higher resolution without dark erosion, while a significantly higher sensitivity with at the same time higher dark erosion can be obtained with developers AR 600-55 and AR 600-548. If CSAR 62 is processed with developer AR 600-548 at a development temperature of about 0 $^{\circ}$ C, even after 10 minutes no erosion is observed at the prolonged development time. Substrates have to be rinsed immediately after development for 30 seconds with stopper and are subsequently dried.